

L Number	Hits	Search Text	DB	Time stamp
1	3	"18249"	EPO; JPO; DERWENT	2003/11/18 14:56
2	669	miyakawa.in.	EPO; JPO; DERWENT	2003/11/18 14:56
3	10	miyakawa.in. and plasma	EPO; JPO; DERWENT	2003/11/18 15:01
4	26	barnes-michael.in. cox-michael-s\$.in. lai-canfeng.in. parks-joun.in.	EPO; JPO; DERWENT	2003/11/18 15:02
5	58	barnes-michael.in. cox-michael-s\$.in. lai-canfeng.in. parks-joun.in.	USPAT; US-PGPUB	2003/11/18 15:02
-	0	((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.) and (anneal\$3 heat\$s) with silylation with cur\$3)	USPAT; US-PGPUB	2003/05/13 11:25
-	0	((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.) and (anneal\$3 heat\$s) same silylation same cur\$3)	USPAT; US-PGPUB	2003/05/13 11:32
-	1	09/502,126	USPAT; US-PGPUB	2003/05/13 11:23
-	3534	atmospher\$3 with pressure with plasma	USPAT; US-PGPUB	2003/05/13 11:26
-	1709	((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.	USPAT; US-PGPUB	2003/05/13 12:34
-	50	(atmospher\$3 with pressure with plasma) and ((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.)	USPAT; US-PGPUB	2003/05/13 11:26
-	6	5578130.URPN.	USPAT;	2003/05/13 11:30
-	3	((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.) and (anneal\$3 heat\$s) same silicon same cur\$3)	USPAT; US-PGPUB	2003/05/13 11:34
-	49	(cur\$3 with chamber) and (anneal\$3 with chamber) and ((silicon silylation) with chamber)	USPAT; US-PGPUB	2003/05/13 12:17
-	8	("4944895" "5047369" "5858457" "5958577" "6048804" "6153511" "6218302" "6284682").PN.	USPAT	2003/05/13 11:57
-	1	"high pressure deposition module"	USPAT; US-PGPUB	2003/05/13 12:33
-	1374	"APCVD"	USPAT; US-PGPUB	2003/05/13 12:39
-	17	"APCVD" and ((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.)	USPAT; US-PGPUB	2003/05/13 12:34
-	464	"APCVD" with plasma	USPAT; US-PGPUB	2003/05/13 12:42
-	1	("APCVD" with plasma) and ((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.)	USPAT; US-PGPUB	2003/05/13 12:39
-	9	"silylation chamber"	USPAT; US-PGPUB	2003/05/13 12:44
-	44	silylation with chamber	USPAT; US-PGPUB	2003/05/13 12:44
-	35	(silylation with chamber) not "silylation chamber"	USPAT; US-PGPUB	2003/05/13 13:05
-	1	("6451118").PN.	USPAT; US-PGPUB	2003/05/13 13:05
-	1667	spin with coating with uniform\$3	USPAT; US-PGPUB	2003/05/13 15:34
-	5	(spin with coating with uniform\$3) and ((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.)	USPAT; US-PGPUB	2003/05/13 15:37
-	0	spin with coating with uniform\$3 with atmospheric with deposit\$3	USPAT; US-PGPUB	2003/05/13 15:35
-	0	spin with coating with uniform\$3 same (atmospheric with deposit\$3)	USPAT; US-PGPUB	2003/05/13 15:36
-	162	(spin with coating with uniform\$3) and (118/\$.ccls.)	USPAT; US-PGPUB	2003/05/13 15:40
-	4	(spin with coating with uniform\$3 with atmospheric) and (118/\$.ccls.)	USPAT; US-PGPUB	2003/05/13 15:40

-	3584	plasma with (atmospheric high) with pressure	EPO; JPO; DERWENT	2003/11/18 11:15
-	1257	plasma with (atmospheric high) with pressure with (coat\$3 deposit\$3 layer film)	EPO; JPO; DERWENT	2003/11/18 11:29
-	380	(plasma with (atmospheric high) with pressure with (coat\$3 deposit\$3 layer film)) and c23c016\$.ipc.	EPO; JPO; DERWENT	2003/11/18 11:30
-	135	(plasma with (atmospheric) with pressure with (coat\$3 deposit\$3 layer film)) and c23c016\$.ipc.	EPO; JPO; DERWENT	2003/11/18 12:17
-	30	(plasma with (atmospheric) with pressure with (coat\$3 deposit\$3 layer film) with (semiconductor dielectric)) and c23c016\$.ipc.	EPO; JPO; DERWENT	2003/11/18 11:20
-	3232	plasma with (atmospheric high) with pressure with (coat\$3 deposit\$3 layer film)	USPAT; US-PGPUB	2003/11/18 11:29
-	20	(plasma with (atmospheric high) with pressure with (coat\$3 deposit\$3 layer film)) and 118/\$.cccls.	EPO; JPO; DERWENT	2003/11/18 12:59
-	330	(plasma with (atmospheric high) with pressure with (coat\$3 deposit\$3 layer film)) and 118/\$.cccls.	USPAT; US-PGPUB	2003/11/18 12:59
-	2	(plasma with (atmospheric high) with pressure with (coat\$3 deposit\$3 layer film)) and 414/\$.cccls.	USPAT; US-PGPUB	2003/11/18 11:31
-	135	(plasma with (atmospheric high) with pressure with (coat\$3 deposit\$3 layer film)) and 156/345\$.cccls.	USPAT; US-PGPUB	2003/11/18 11:31
-	41	(plasma with (atmospheric high) with pressure with (coat\$3 deposit\$3 layer film)) and 118/719.cccls.	USPAT; US-PGPUB	2003/11/18 11:31
-	1	("5319247").PN.	USPAT; US-PGPUB	2003/11/18 11:53
-	33	5319247.URPN.	USPAT	2003/11/18 11:45
-	1154	"atmospheric pressure" with plasma with (deposit\$3 coat\$3 film layer)	USPAT; US-PGPUB	2003/11/18 11:54
-	376	"atmospheric pressure" with plasma with (deposit\$3 coat\$3 film layer)	EPO; JPO; DERWENT	2003/11/18 11:54
-	34	("atmospheric pressure" with plasma with (deposit\$3 coat\$3 film layer)) same semiconductor	EPO; JPO; DERWENT	2003/11/18 11:54
-	215	("atmospheric pressure" with plasma with (deposit\$3 coat\$3 film layer)) same semiconductor	USPAT; US-PGPUB	2003/11/18 11:59
-	330	(plasma with (atmospheric high) with pressure with (coat\$3 deposit\$3 layer film)) and 118/\$.cccls.	USPAT; US-PGPUB	2003/11/18 12:17
-	2	(in\$lline same cluster) and c23c016\$.ipc.	EPO; JPO; DERWENT	2003/11/18 12:18
-	9	(in\$lline same cluster) and 118/719.cccls.	USPAT; US-PGPUB	2003/11/18 12:18
-	24	(plasma with "atmospheric pressure") and 118/719.cccls.	USPAT; US-PGPUB	2003/11/18 13:53
-	18	5651867.URPN.	USPAT	2003/11/18 13:07
-	1	("6342275").PN.	USPAT; US-PGPUB	2003/11/18 14:56